

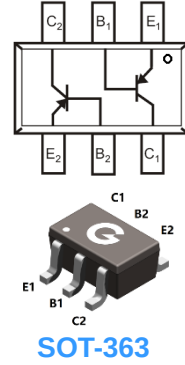
Features

- Epitaxial die construction
- Ultra-small surface mount package

HF

Mechanical Data

- Case: SOT-363
- Molding compound: UL flammability classification rating 94V-0
- Terminal s: Tin-plated; solderability per MIL-STD-202, Method 208



Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BC858AS	SOT-363	3000 pcs / Tape & Reel	3J
BC858BS	SOT-363	3000 pcs / Tape & Reel	3K
BC858CS	SOT-363	3000 pcs / Tape & Reel	3L

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-30	V
Collector-Emitter Voltage	V _{CE0}	-30	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current (Continuous)	I _C	-100	mA
Collector Current (Pulse)	I _{CM}	-200	mA

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation (T _A = 25°C)	P _D	300	mW
Thermal Resistance Junction-to-Air *1	R _{θJA}	320	°C/W
Thermal Resistance Junction-to-Case *1	R _{θJC}	210	°C/W
Thermal Resistance Junction-to-Lead *1	R _{θJL}	240	°C/W
Operating Junction Temperature	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Note 1: The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}, I_B = 0$	-30	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	-30	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -1\mu\text{A}, I_C = 0$	-5	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -30\text{V}, I_E = 0$	-	-	-15	nA
Emitter-base Cut-off Current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$	-	-	-100	nA
DC Current Gain	h_{FE}	$V_{CE} = -5\text{V}, I_C = -2\text{mA}$				
		BC858AS	125	-	250	-
		BC858BS	220	-	475	-
		BC858CS	420	-	800	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -10\text{mA}, I_B = -0.5\text{mA}$	-	-	-0.3	V
		$I_C = -100\text{mA}, I_B = -5\text{mA}$	-	-	-0.65	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -10\text{mA}, I_B = -0.5\text{mA}$	-	-0.7	-	V
		$I_C = -100\text{mA}, I_B = -5\text{mA}$	-	-0.85	-	V
Base-Emitter Voltage	$V_{BE(ON)}$	$V_{CE} = -5\text{V}, I_C = -2\text{mA}$	-0.6	-	-0.75	V
		$V_{CE} = -5\text{V}, I_C = -10\text{mA}$	-	-	-0.82	V
Transition Frequency	f_T	$V_{CE} = -5\text{V}, I_C = -10\text{mA}$ $f = 100\text{MHz}$	100	-	-	-
Output Capacitance	C_{obo}	$V_{CB} = -10\text{V}, I_E = I_C = 0$ $f = 1\text{MHz}$	-	-	4.5	pF

Ratings and Characteristic Curves-BC858AS (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

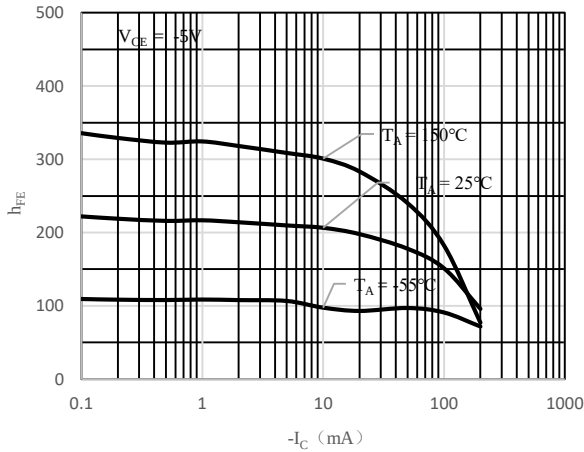


Fig 1 h_{FE} vs. I_C

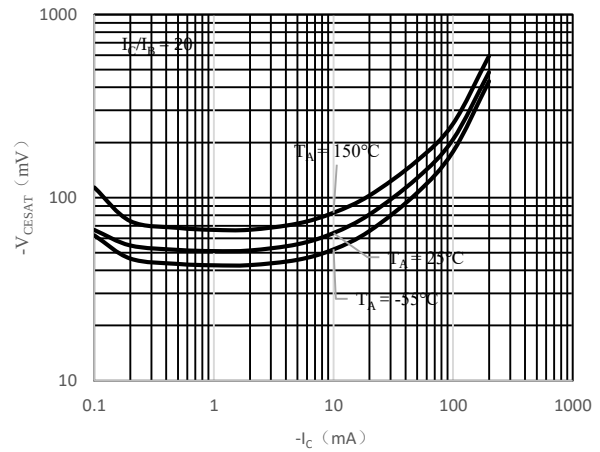


Fig 2 $V_{CE(sat)}$ vs. I_C

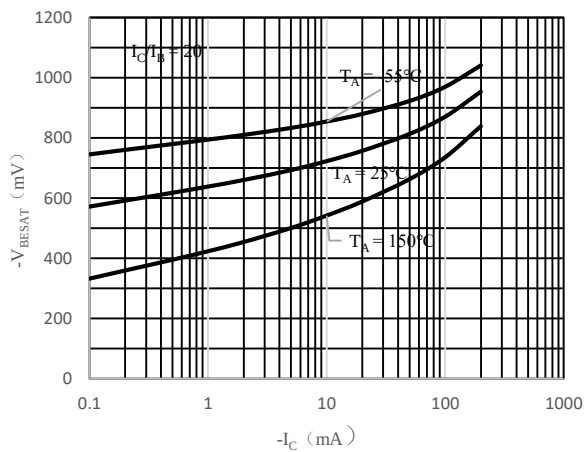


Fig 3 $V_{BE(sat)}$ vs. I_C

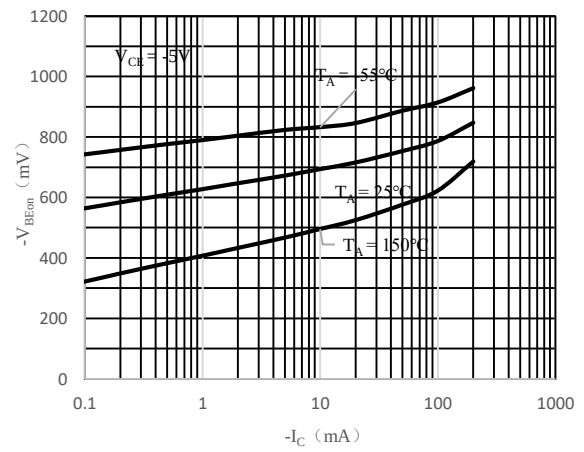


Fig 4 $V_{BE(on)}$ vs. I_C

Ratings and Characteristic Curves-BC858BS (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

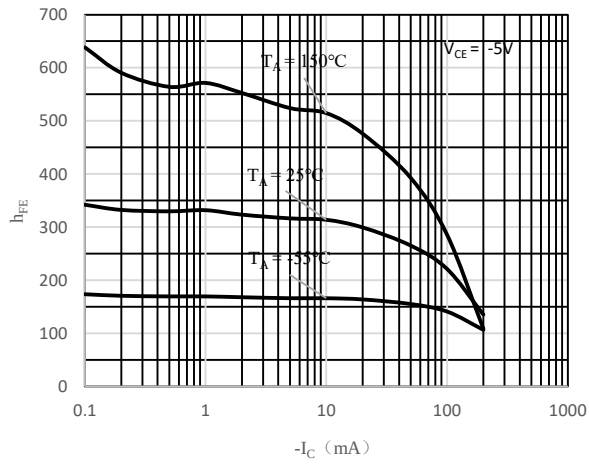


Fig 1 h_{FE} vs. I_C

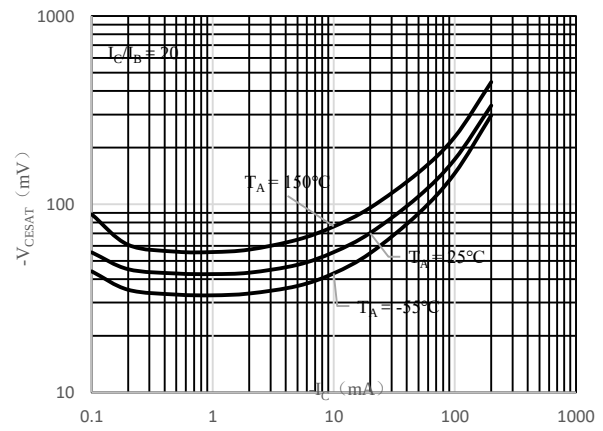


Fig 2 $V_{CE(sat)}$ vs. I_C

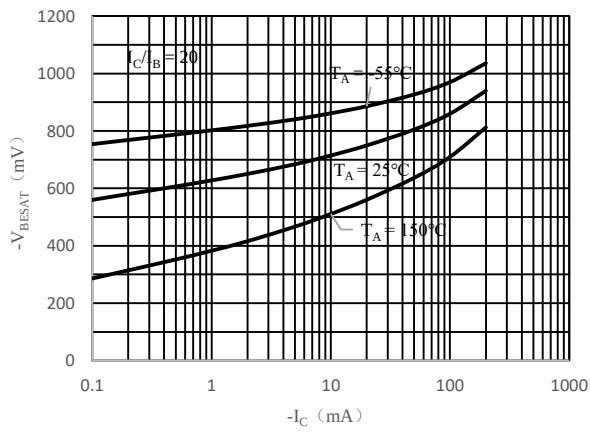


Fig 3 $V_{BE(sat)}$ vs. I_C

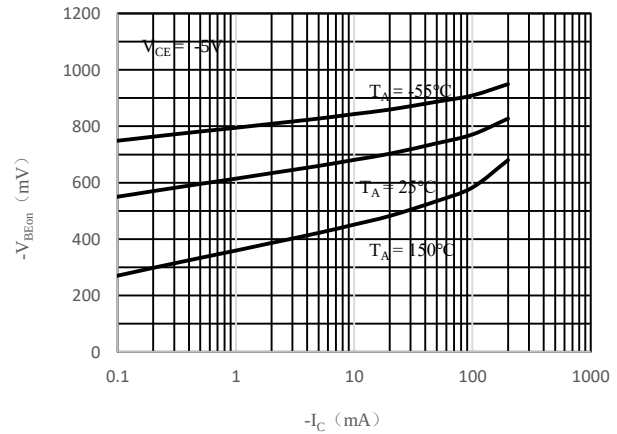


Fig 4 $V_{BE(on)}$ vs. I_C

Ratings and Characteristic Curves-BC858CS (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

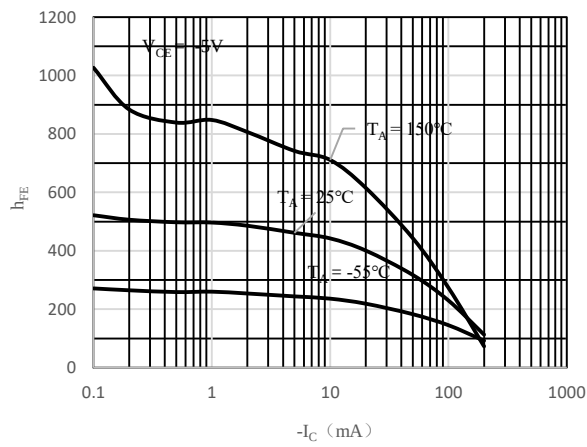


Fig 1 h_{FE} vs. I_C

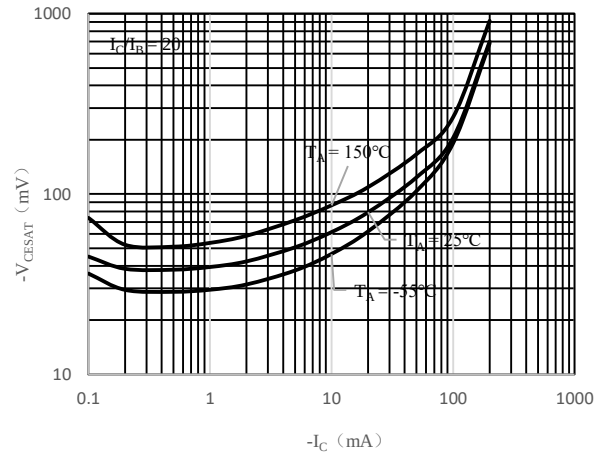


Fig 2 $V_{CE(sat)}$ vs. I_C

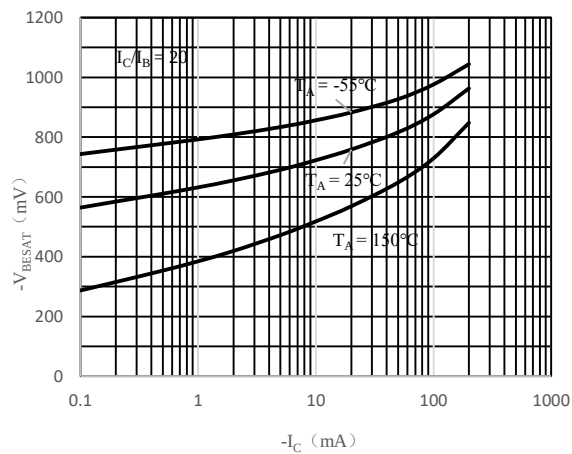


Fig 3 $V_{BE(sat)}$ vs. I_C

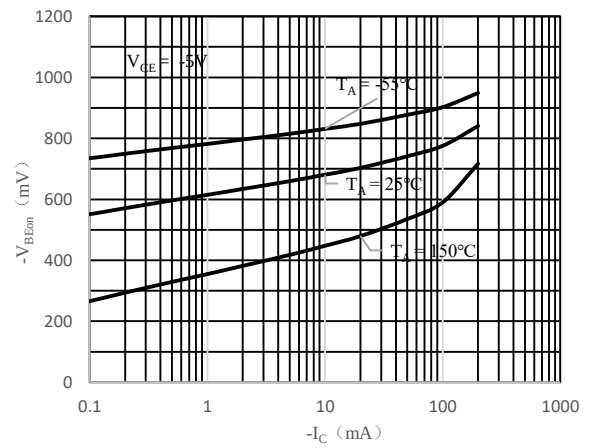
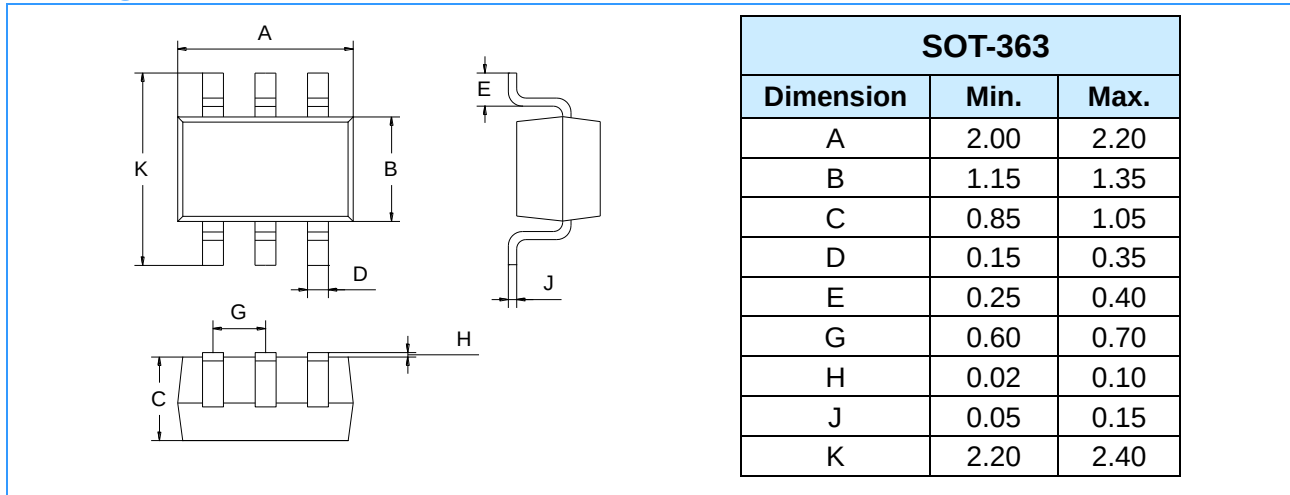
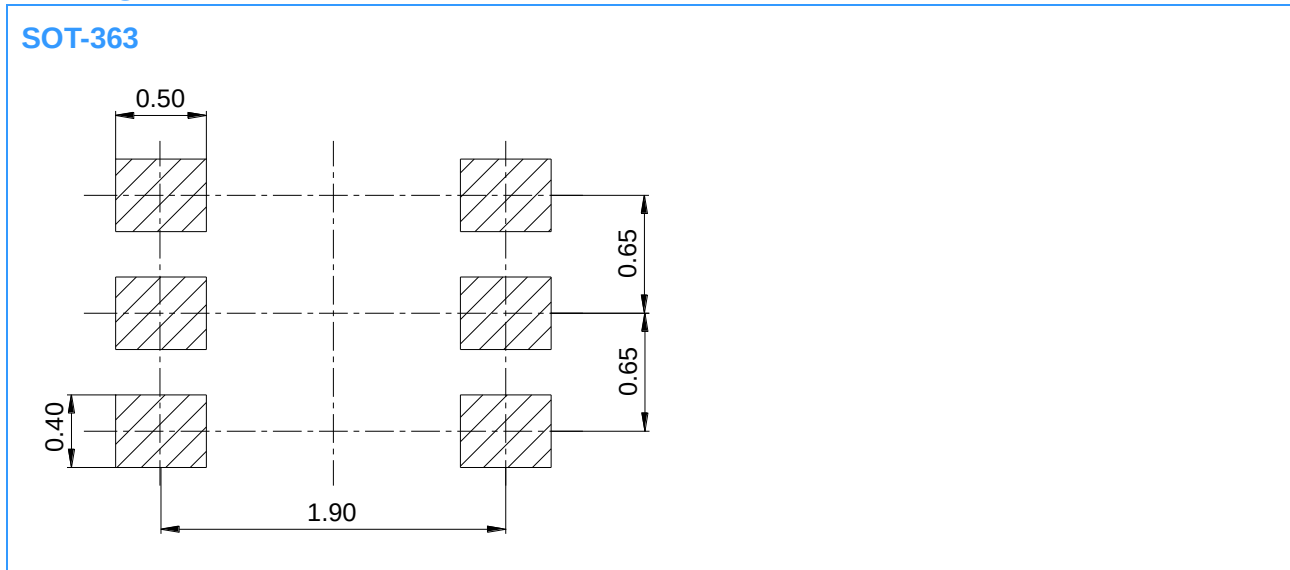


Fig 4 $V_{BE(ON)}$ vs. I_C

Package Outline Dimensions (Unit: mm)



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